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PTO/SB/08A (10-01)

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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown 10765619
	Filing Date	Even Date Herewith
	First Name of Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 1 of 3	Attorney Docket No: 1303.033US2	

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Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 2 of 3

Attorney Docket No: 1303.033US2

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Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

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